

IN THE SPECIFICATION

Please amend the paragraph at page 4, lines 10-17 as follows:

At this time, since an SiGe layer is included in the region of the depletion layer D1, a collector-base junction breakdown voltage (BV_{cbo}) of the bipolar transistor is lowered. This is because an energy gap of silicon is about 1.1 eV while energy gap of germanium is low at about 0.67eV, and a breakdown field of silicon is about $30 \text{ V}/\mu\text{m}$ while a breakdown field of germanium is low at about $8\text{V}/\mu\text{m}$.